



PNP SMALL SIGNAL TRANSISTOR IN SOT23

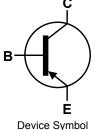
Features

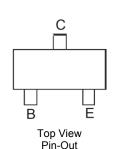
- Ideally Suited for Automatic Insertion
- Complementary NPN Types: BC846 BC848
- For switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)







Top View

Ordering Information (Notes 4 & 5)

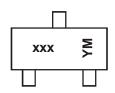
Product	Compliance	Marking	Reel Size (inches)	Quantity per Reel
BC856A-7-F	AEC-Q101	K3A	7	3,000
BC856AQ-7-F	Automotive	K3A	7	3,000
BC856B-7-F	AEC-Q101	K3B	7	3,000
BC856BQ-7-F	Automotive	K3B	7	3,000
BC856B-13-F	AEC-Q101	K3B	13	10,000
BC856BQ-13-F	Automotive	K3B	13	10,000
BC857A-7-F	AEC-Q101	K3A	7	3,000

Product	Compliance	Marking	Reel Size (inches)	Quantity per Reel
BC857B-7-F	AEC-Q101	K3B	7	3,000
BC857BQ-7-F	Automotive	K3B	7	3,000
BC857B-13-F	AEC-Q101	K3B	13	10,000
BC857C-7-F	AEC-Q101	K3G	7	3,000
BC857C-13-F	AEC-Q101	K3G	13	10,000
BC858A-7-F	AEC-Q101	K3A	7	3,000
BC858B-7-F	AEC-Q101	K3B	7	3,000
BC858C-7-F	AEC-Q101	K3G	7	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. Tape width is 8mm. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



xxx = Product Type Marking Code
(Please see Ordering Information)
YM = Date Code Marking
Y or Y = Year (ex: A = 2013)
M or M = Month (ex: 9 = September)

Date Code Key

Year	2010	20	011	2012	2	013	2014	- :	2015	2016		2017
Code	X		Υ	Z		Α	В		С	D		Е
				ı						1		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteris	tic	Symbol	Value	Unit
	BC856		-80	
Collector-Base Voltage	BC857	V _{CBO}	-50	V
	BC858		-30	
	BC856		-65	
Collector-Emitter Voltage	BC857	$V_{\sf CEO}$	-45	V
	BC858		-30	
Emitter-Base Voltage		V_{EBO}	-5.0	V
Continuous Collector Current		Ic	-100	mA
Peak Collector Current		I _{CM}	-200	mA
Peak Emitter Current		I _{EM}	-200	mA
Peak Base Current		I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)		310	mW
Power Dissipation	(Note 7)	P _D	350	IIIVV
Thermal Resistance, Junction to Ambient	(Note 6)	Б	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	C/VV
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	350	°C/W
Operating and Storage Temperature Range		T_{J} , T_{STG}	-65 to +150	°C

ESD Ratings (Note 9)

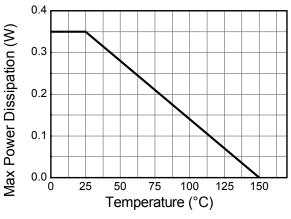
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

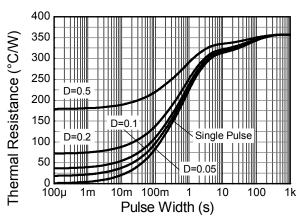
Notes:

^{6.} For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air 7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
8. Thermal resistance from junction to solder-point (at the end of the leads).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



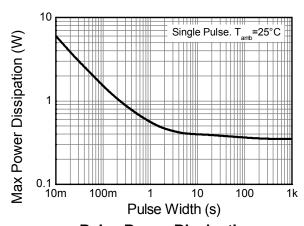
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Min	Тур	Max	Unit	Test Condition
		BC856		-80				
Collector-Base Breakdown V	oltage	BC857	BV _{CBO}	-50	l —	_	V	$I_{C} = -10 \mu A$
	· ·	BC858		-30				
0 11 1 5 11 5 11	\ / II	BC856		-65				
Collector-Emitter Breakdown Voltage		BC857	BV_{CEO}	-45	_	_	V	$I_{\rm C} = -10 {\rm mA}$
(Note 10) BC858		BC858		-30				
Emitter-Base Breakdown Vo	Itage		BV _{EBO}	-5	_	-	V	$I_E = -1\mu A$
Collector Cutoff Current			_			-15	nA	V _{CB} = -30V
Collector Cutoff Current			Ісво	ı	_	-4	μΑ	$V_{CB} = -30V, T_{J} = +150^{\circ}C$
		BC856				-15		V _{CE} = -80V
Collector Emitter Cutoff Curr	ent	BC857	I _{CES}	_	_	-15	nA	V _{CE} = -50V
		BC858				-15		$V_{CE} = -30V$
Emitter-Base Cutoff Current			I _{EBO}	_	_	-100	nA	V _{EB} = -5V
Carall Cianal Compant Caia	BC856A / E	3C857A / BC858A			200			
Small Signal Current Gain (Note 10)	BC856B / E	3C857B / BC858B	h _{fe}	_	330	_	_	
(Note 10)	BC857	7C / BC858C	1		600			
	BC856A / E	3C857A / BC858A			2.7			
Input Impedance (Note 10)	BC856B / E	3C857B / BC858B	h _{ie}	_	4.5	5 —	kΩ	
	BC857C / BC858C				8.7			$I_C = -2.0$ mA, $V_{CE} = -5V$ f = 1.0kHz
Output Admittance	BC856A / E	856A / BC857A / BC858A			18		μS	
(Note 10)	BC856B / BC857B / BC858B		h _{oe}	_	30			
(Note 10)		7C / BC858C			60			
Reverse Voltage Transfer	BC856A / E	3C857A / BC858A			1.5x10 ⁻⁴		_	
Ratio (Note 10)		3C857B / BC858B	h _{re}	_	2x10 ⁻⁴	1 —		
Italio (Note 10)		7C / BC858C			3x10 ⁻⁴			
		3C857A / BC858A		125	180	250		
DC Current Gain (Note 10)		3C857B / BC858B	h_{FE}	220	290	475	_	$I_C = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
	BC85	7C / BC858C		420	520	800		
Collector-Emitter Saturation	Voltago (Noto 1	n)	\/		-75	-300	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Collector-Emitter Saturation	voltage (Note 1)	5)	V _{CE(sat)}	_	-250	-650	IIIV	$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Page Emitter Turn On Voltag	ro (Noto 10)		V	-600	-650	-750	mV	$I_C = -2mA, V_{CE} = -5V$
Base-Emitter Turn-On Voltag	ge (Note 10)		V _{BE(on)}	1	_	-820	IIIV	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
Base-Emitter Saturation Volt	ago (Noto 10)		\/·		-700		mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Base-Emitter Saturation voit	age (Note 10)		V _{BE(sat)}		-850		IIIV	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$
Output Capacitance			C _{obo}		3	_	pF	V _{CB} = -10V, f = 1.0MHz
Transition Frequency			f _T	100	200	_	MHz	$V_{CE} = -5V, I_{C} = -10mA,$ f = 100MHz
Noise Figure			NF	_	2	10	dB	V_{CE} = -5V, I_{C} = -200 μ A R_{S} = 2k Ω , f = 1kHz Δf = 200Hz

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

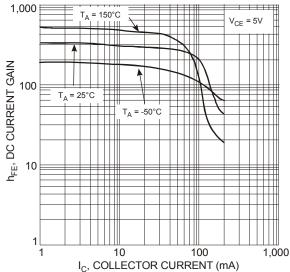
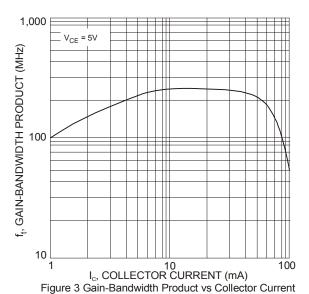


Figure 1 Typical DC Current Gain vs. Collector Current



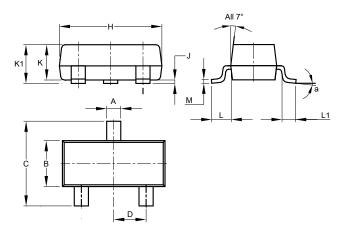
 $\begin{array}{c} 0.5 \\ \begin{array}{c} \frac{l_C}{l_B} = 10 \\ \end{array} \\ 0.4 \\ \begin{array}{c} 0.4 \\ \end{array} \\ \begin{array}{c} \frac{l_C}{l_B} = 10 \\ \end{array} \\ 0.2 \\ \begin{array}{c} T_A = 150^\circ C \\ \end{array} \\ \begin{array}{c} T_A = 25^\circ C \\ \end{array} \\ \begin{array}{c} T_A = -50^\circ C \\ \end{array} \\ \begin{array}{c} 0.1 \\ \end{array} \\ \begin{array}{c} T_A = -50^\circ C \\ \end{array}$

Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

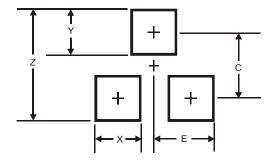
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Min Max Ty						
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а		8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
Е	1.35



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